NSN 5961-01-093-0852

Transistor - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-093-0852 **Inclosure Material:** Metal **Overall Length:** Between 0.250 inches and 0.340 inches Overall Diameter: 0.620 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-66 **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 130.0 breakdown voltage, collector-to-base, emitter open and 120.0 breakdown voltage, collector to emitter, sustained and 5.0 breakdown voltage, emitter-to-base, collector open **Current Rating Per Characteristic:** Between 2.00 amperes source cutoff current and 4.00 amperes source cutoff current **Power Rating Per Characteristic:** 40.0 watts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Terminal Type And Quantity:** 1 case and 2 pin **Specification Data:** 80131-release6483 professional/industrial association specification Shelf Life: N/a **Unit Of Measure: Demilitarization:**

No **Fiig:**

•

A110a0